

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

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| Sheet | 1 | of | 2 |
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Complete If Known

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|------------------------|------------------|
| Application Number | 10/816,282 |
| Filing Date | March 31, 2004 |
| First Named Inventor | Peter L.D. Chang |
| Art Unit | 2818 |
| Examiner Name | Ho, Tu Tu V. |
| Attorney Docket Number | 42P18252 |

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

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**Examiner
Signature**

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| Date | |
| Considered | |

Dec-2005

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

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Based on PTO/SB/D8A (08-03) as modified by Blakely, Solokoff, Taylor & Zalman (w/ 08/11/2003).

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| NON PATENT LITERATURE DOCUMENTS | | | | |
|---------------------------------|--------------|---|--|----|
| Examiner Initials* | Cite No.† | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | | T‡ |
| TH | | Nowak EJ, et al., "Turning Silicon On Its Edge - Overcoming silicon scaling barriers with double-gate and FinFET technology," IEEE Circuits and Devices Mag. vol. 20, no. 1, January 2004, pgs 20-31. | | |
| TH | | Fried, DM, et al. "Improved Independent Gate N-Type FinFET Fabrication and Characterization," IEEE Electron Device Letters, vol. 24, no. 9, September 2003, pages 592-594. | | |
| TH | | Fried, DM, et al. "A Fin-Type Independent-Double-Gate NFET," Device Research Conference, 2003 June, IEEE, 23 June 2003, pages 45-46. | | |
| TH | | PCT Search Report, Int'l application no. PCT/US2005/010164, mailed 07-27-2005, 5 pgs. | | |
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| Examiner Signature | TU TU HIO | Date Considered | Dec. 2005 |
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